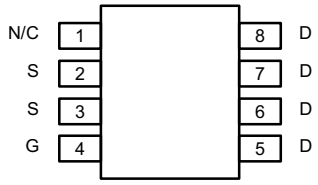
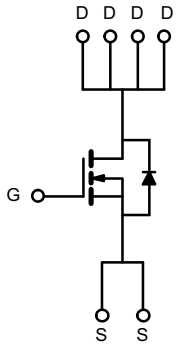
N-Channel Enhancement-Mode MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(ON)}$ (Ω)	I_D (A)
200	1.0 @ V_{GS} = 10 V	±1.0

SO-8



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 150°C)[A]	T_A = 25°C	I_D	±1.0	A
	T_A = 70°C		±0.8	
Pulsed Drain Current		I_{DM}	±10	
Avalanche Current		I_{AS}	5	
Single Avalanche Energy		E_{AS}	1.3	mJ
Continuous Source Current (Diode Conduction)[A]		I_S	1.0	A
Maximum Power Dissipation[A]	T_A = 25°C	P_D	2.5	W
	T_A = 70°C		1.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Maximum Junction-to-Ambient[A]	R_{thJA}	50	°C/W

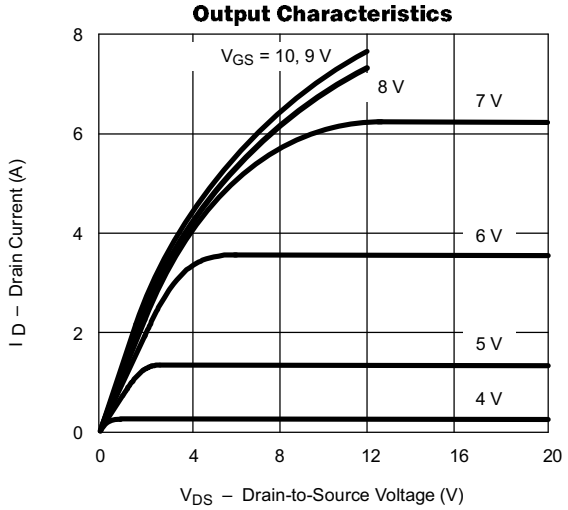
Notes
A. Surface Mounted on FR4 Board, t ≤ 10 sec.

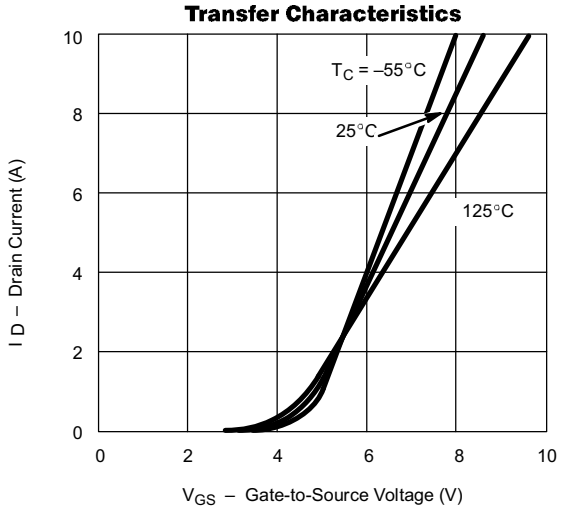
Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70123.

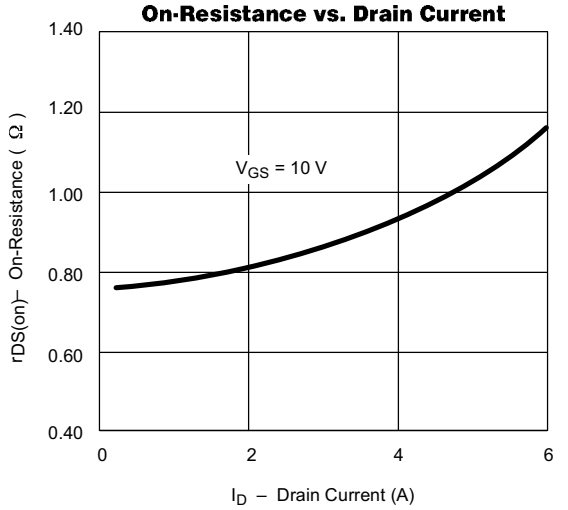
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)						
PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP[A]	MAX	UNIT
STATIC						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V	2		±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 160 V, V_{GS} = 0 V			2	μA
		V_{DS} = 160 V, V_{GS} = 0 V, T_J = 55°C			25	
On-State Drain Current[B]	$I_{D(on)}$	V_{DS} ≥ 10 V, V_{GS} = 10 V	5.0			A
Drain-Source On-State Resistance[B]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 1.0 A		0.8	1.0	Ω
Forward Transconductance[B]	g_{fs}	V_{DS} = 15 V, I_D = 1.0 A		1.5		S
Diode Forward Voltage[B]	V_{SD}	I_S = 1.0 A, V_{GS} = 0 V		0.7	1.2	V
DYNAMIC[A]						
Total Gate Charge	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 1.0 A		8.6	16	nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			3.2		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 100 V, R_L = 100 Ω I_D ≅ 1.0 A, V_{GEN} = 10 V, R_G = 6 Ω		7	14	ns
Rise Time	t_r			12	24	
Turn-Off Delay Time	$t_{d(off)}$			26	50	
Fall Time	t_f			15	30	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.0 A, di/dt = 100 A/μs		130		

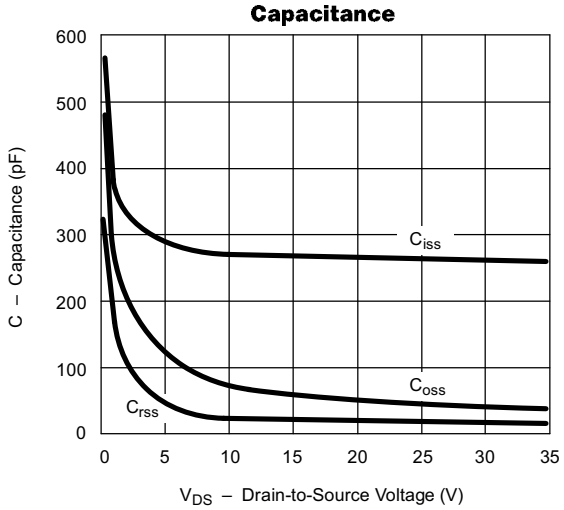
Notes
A. Guaranteed by design, not subject to production testing.
B. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

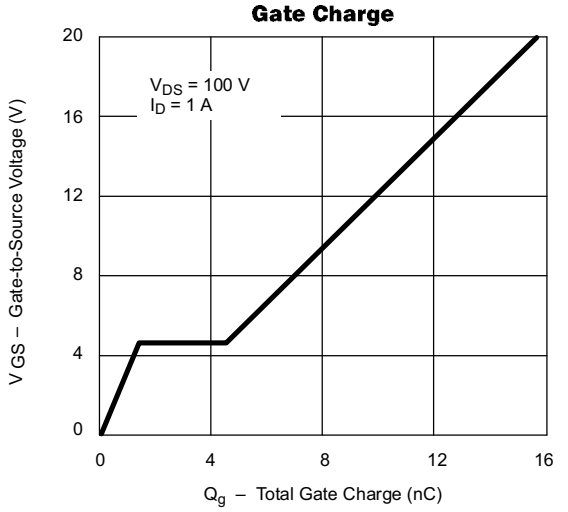
TYPICAL CHARACTERISTICS (25°C UNLESS OTHERWISE NOTED)

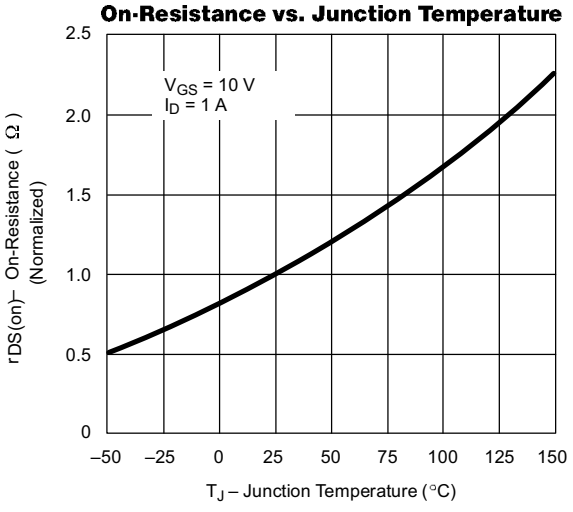






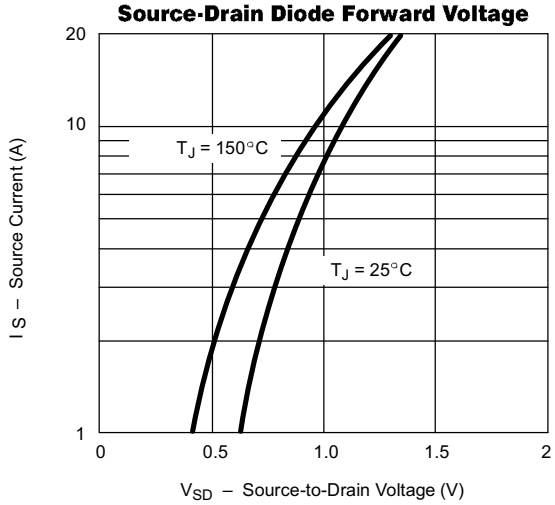




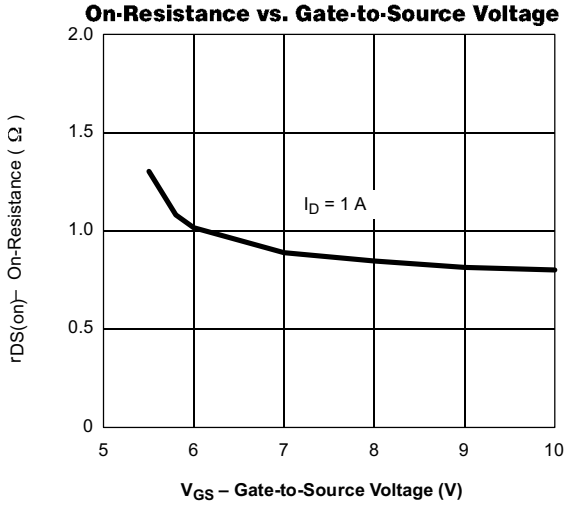


TYPICAL CHARACTERISTICS (25°C UNLESS OTHERWISE NOTED)

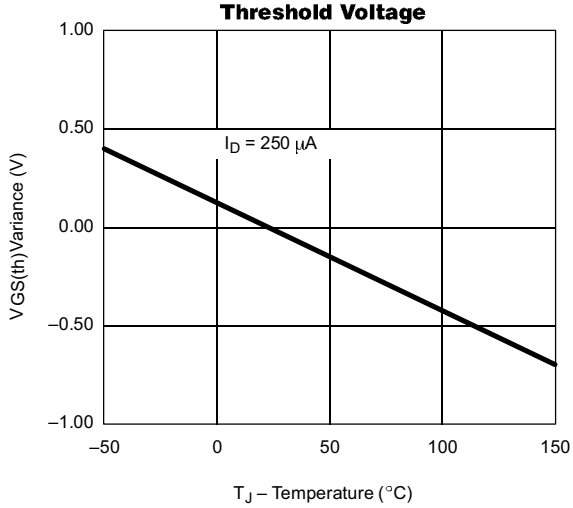
Source-Drain Diode Forward Voltage



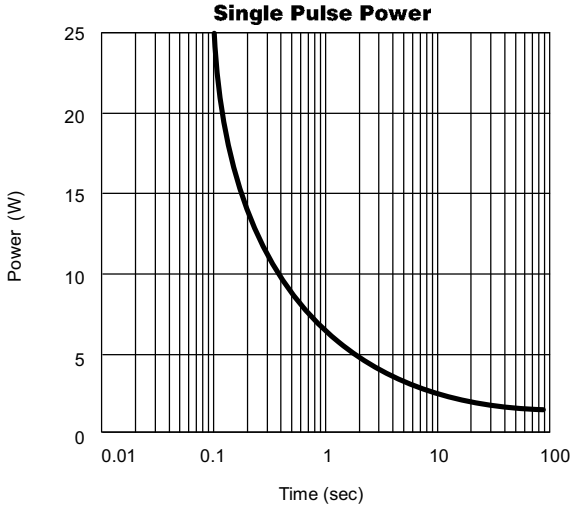
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient